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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	147456
Number of I/O	97
Number of Gates	1000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p1000-2fg144

Table 2-43 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 3.0\text{ V}$
Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.66	7.20	0.04	1.00	0.43	7.34	6.29	2.27	2.34	9.57	8.52	ns
	–1	0.56	6.13	0.04	0.85	0.36	6.24	5.35	1.93	1.99	8.14	7.25	ns
	–2	0.49	5.38	0.03	0.75	0.32	5.48	4.69	1.70	1.75	7.15	6.36	ns
4 mA	Std.	0.66	7.20	0.04	1.00	0.43	7.34	6.29	2.27	2.34	9.57	8.52	ns
	–1	0.56	6.13	0.04	0.85	0.36	6.24	5.35	1.93	1.99	8.14	7.25	ns
	–2	0.49	5.38	0.03	0.75	0.32	5.48	4.69	1.70	1.75	7.15	6.36	ns
6 mA	Std.	0.66	4.50	0.04	1.00	0.43	4.58	3.82	2.58	2.88	6.82	6.05	ns
	–1	0.56	3.83	0.04	0.85	0.36	3.90	3.25	2.19	2.45	5.80	5.15	ns
	–2	0.49	3.36	0.03	0.75	0.32	3.42	2.85	1.92	2.15	5.09	4.52	ns
8 mA	Std.	0.66	4.50	0.04	1.00	0.43	4.58	3.82	2.58	2.88	6.82	6.05	ns
	–1	0.56	3.83	0.04	0.85	0.36	3.90	3.25	2.19	2.45	5.80	5.15	ns
	–2	0.49	3.36	0.03	0.75	0.32	3.42	2.85	1.92	2.15	5.09	4.52	ns
12 mA	Std.	0.66	3.16	0.04	1.00	0.43	3.22	2.58	2.79	3.22	5.45	4.82	ns
	–1	0.56	2.69	0.04	0.85	0.36	2.74	2.20	2.37	2.74	4.64	4.10	ns
	–2	0.49	2.36	0.03	0.75	0.32	2.40	1.93	2.08	2.41	4.07	3.60	ns
16 mA	Std.	0.66	3.16	0.04	1.00	0.43	3.22	2.58	2.79	3.22	5.45	4.82	ns
	–1	0.56	2.69	0.04	0.85	0.36	2.74	2.20	2.37	2.74	4.64	4.10	ns
	–2	0.49	2.36	0.03	0.75	0.32	2.40	1.93	2.08	2.41	4.07	3.60	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-58 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard I/O Banks

2.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max., V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.7	1.7	3.6	0.7	1.7	2	2	16	18	10	10
4 mA	−0.3	0.7	1.7	3.6	0.7	1.7	4	4	16	18	10	10
6 mA	−0.3	0.7	1.7	3.6	0.7	1.7	6	6	32	37	10	10
8 mA	−0.3	0.7	1.7	3.6	0.7	1.7	8	8	32	37	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

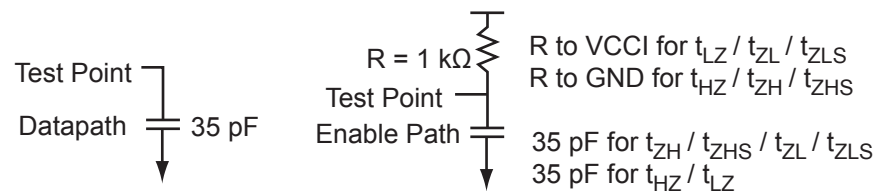


Figure 2-8 • AC Loading

Table 2-59 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	2.5	1.2	35

Note: *Measuring point = Vtrip. See Table 2-22 on page 2-22 for a complete table of trip points.

Table 2-62 • 2.5 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	8.28	0.04	1.30	0.43	7.41	8.28	2.25	2.07	9.64	10.51	ns
	–1	0.56	7.04	0.04	1.10	0.36	6.30	7.04	1.92	1.76	8.20	8.94	ns
	–2	0.49	6.18	0.03	0.97	0.32	5.53	6.18	1.68	1.55	7.20	7.85	ns
6 mA	Std.	0.66	4.85	0.04	1.30	0.43	4.65	4.85	2.59	2.71	6.88	7.09	ns
	–1	0.56	4.13	0.04	1.10	0.36	3.95	4.13	2.20	2.31	5.85	6.03	ns
	–2	0.49	3.62	0.03	0.97	0.32	3.47	3.62	1.93	2.02	5.14	5.29	ns
8 mA	Std.	0.66	4.85	0.04	1.30	0.43	4.65	4.85	2.59	2.71	6.88	7.09	ns
	–1	0.56	4.13	0.04	1.10	0.36	3.95	4.13	2.20	2.31	5.85	6.03	ns
	–2	0.49	3.62	0.03	0.97	0.32	3.47	3.62	1.93	2.02	5.14	5.29	ns
12 mA	Std.	0.66	3.21	0.04	1.30	0.43	3.27	3.14	2.82	3.11	5.50	5.38	ns
	–1	0.56	2.73	0.04	1.10	0.36	2.78	2.67	2.40	2.65	4.68	4.57	ns
	–2	0.49	2.39	0.03	0.97	0.32	2.44	2.35	2.11	2.32	4.11	4.02	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-63 • 2.5 V LVCMOS Low Slew

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$, Worst-Case $V_{CCI} = 2.3\text{ V}$
 Applicable to Standard Plus I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	10.84	0.04	1.30	0.43	10.64	10.84	2.26	1.99	12.87	13.08	ns
	–1	0.56	9.22	0.04	1.10	0.36	9.05	9.22	1.92	1.69	10.95	11.12	ns
	–2	0.49	8.10	0.03	0.97	0.32	7.94	8.10	1.68	1.49	9.61	9.77	ns
6 mA	Std.	0.66	7.37	0.04	1.30	0.43	7.50	7.36	2.59	2.61	9.74	9.60	ns
	–1	0.56	6.27	0.04	1.10	0.36	6.38	6.26	2.20	2.22	8.29	8.16	ns
	–2	0.49	5.50	0.03	0.97	0.32	5.60	5.50	1.93	1.95	7.27	7.17	ns
8 mA	Std.	0.66	7.37	0.04	1.30	0.43	7.50	7.36	2.59	2.61	9.74	9.60	ns
	–1	0.56	6.27	0.04	1.10	0.36	6.38	6.26	2.20	2.22	8.29	8.16	ns
	–2	0.49	5.50	0.03	0.97	0.32	5.60	5.50	1.93	1.95	7.27	7.17	ns
12 mA	Std.	0.66	5.63	0.04	1.30	0.43	5.73	5.51	2.83	3.01	7.97	7.74	ns
	–1	0.56	4.79	0.04	1.10	0.36	4.88	4.68	2.41	2.56	6.78	6.59	ns
	–2	0.49	4.20	0.03	0.97	0.32	4.28	4.11	2.11	2.25	5.95	5.78	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-77 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard Plus I/O Banks

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	2	2	16	13	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4	33	25	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

Table 2-78 • Minimum and Maximum DC Input and Output Levels
Applicable to Standard I/O Banks

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL ¹	IIH ²
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA ³	Max. mA ³	μA ⁴	μA ⁴
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10

Notes:

1. IIL is the input leakage current per I/O pin over recommended operation conditions where $-0.3\text{ V} < V_{IN} < V_{IL}$.
2. IIH is the input leakage current per I/O pin over recommended operating conditions $V_{IH} < V_{IN} < V_{CCI}$. Input current is larger when operating outside recommended ranges.
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

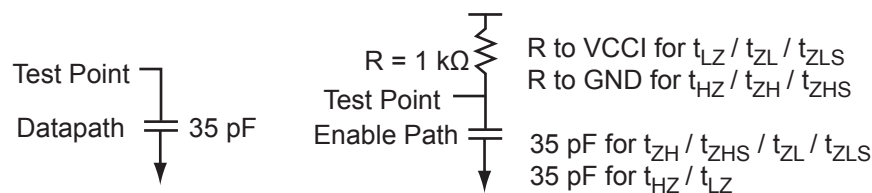


Figure 2-10 • AC Loading

Table 2-79 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	1.5	0.75	35

Note: *Measuring point = V_{trip} . See Table 2-22 on page 2-22 for a complete table of trip points.

3.3 V PCI, 3.3 V PCI-X

Peripheral Component Interface for 3.3 V standard specifies support for 33 MHz and 66 MHz PCI Bus applications.

Table 2-86 • Minimum and Maximum DC Input and Output Levels

3.3 V PCI/PCI-X	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL	IIH
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max., V	Min. V	mA	mA	Max. mA ¹	Max. mA ¹	μA ²	μA ²
Per PCI specification	Per PCI curves										10	10

Notes:

1. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
2. Currents are measured at 85°C junction temperature.

AC loadings are defined per the PCI/PCI-X specifications for the datapath; Microsemi loadings for enable path characterization are described in [Figure 2-11](#).

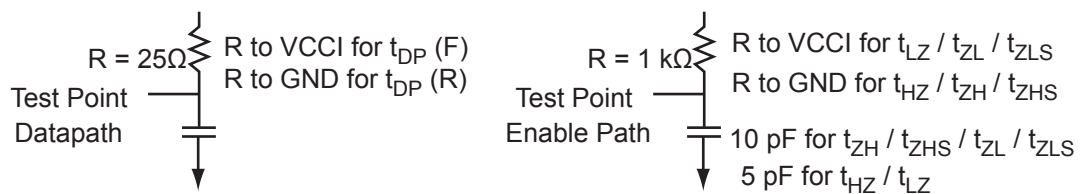


Figure 2-11 • AC Loading

AC loadings are defined per PCI/PCI-X specifications for the datapath; Microsemi loading for tristate is described in [Table 2-87](#).

Table 2-87 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)	C _{LOAD} (pF)
0	3.3	0.285 * V _{CCI} for $t_{DP}(R)$ 0.615 * V _{CCI} for $t_{DP}(F)$	10

Note: *Measuring point = V_{trip} . See [Table 2-22 on page 2-22](#) for a complete table of trip points.

B-LVDS/M-LVDS

Bus LVDS (B-LVDS) and Multipoint LVDS (M-LVDS) specifications extend the existing LVDS standard to high-performance multipoint bus applications. Multidrop and multipoint bus configurations may contain any combination of drivers, receivers, and transceivers. Microsemi LVDS drivers provide the higher drive current required by B-LVDS and M-LVDS to accommodate the loading. The drivers require series terminations for better signal quality and to control voltage swing. Termination is also required at both ends of the bus since the driver can be located anywhere on the bus. These configurations can be implemented using the TRIBUF_LVDS and BIBUF_LVDS macros along with appropriate terminations. Multipoint designs using Microsemi LVDS macros can achieve up to 200 MHz with a maximum of 20 loads. A sample application is given in Figure 2-13. The input and output buffer delays are available in the LVDS section in Table 2-92.

Example: For a bus consisting of 20 equidistant loads, the following terminations provide the required differential voltage, in worst-case Industrial operating conditions, at the farthest receiver: $R_S = 60\ \Omega$ and $R_T = 70\ \Omega$, given $Z_0 = 50\ \Omega$ (2") and $Z_{stub} = 50\ \Omega$ (~1.5").

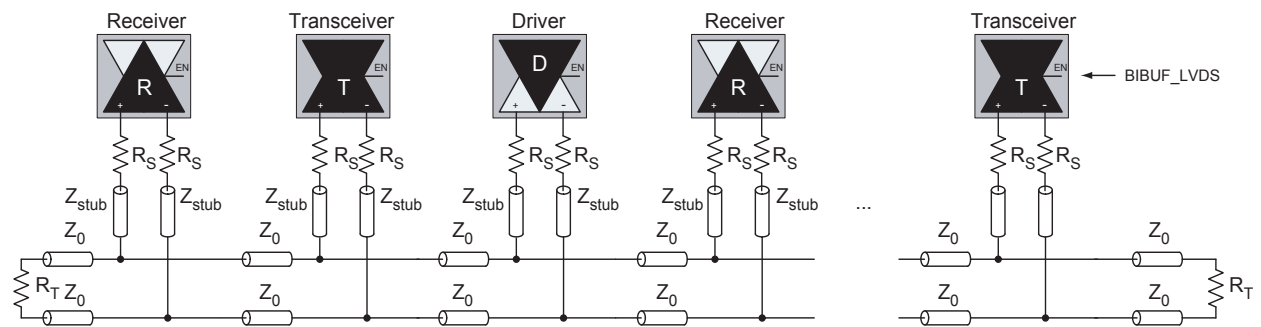


Figure 2-13 • B-LVDS/M-LVDS Multipoint Application Using LVDS I/O Buffers

LVPECL

Low-Voltage Positive Emitter-Coupled Logic (LVPECL) is another differential I/O standard. It requires that one data bit be carried through two signal lines. Like LVDS, two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in Figure 2-14. The building blocks of the LVPECL transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVDS implementation because the output standard specifications are different.

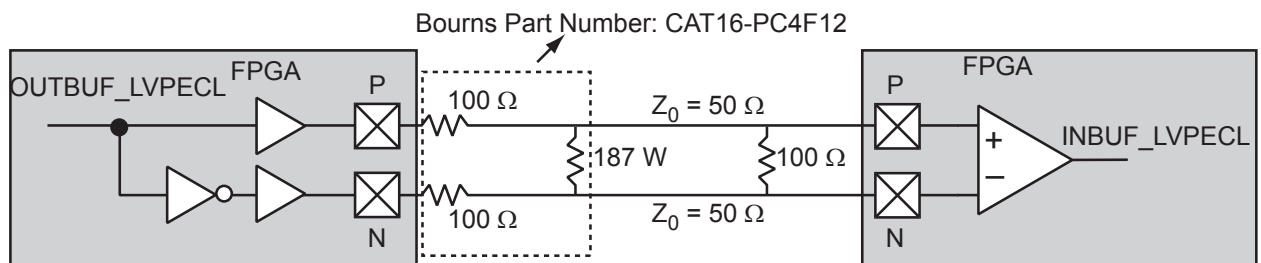


Figure 2-14 • LVPECL Circuit Diagram and Board-Level Implementation

Output DDR Module

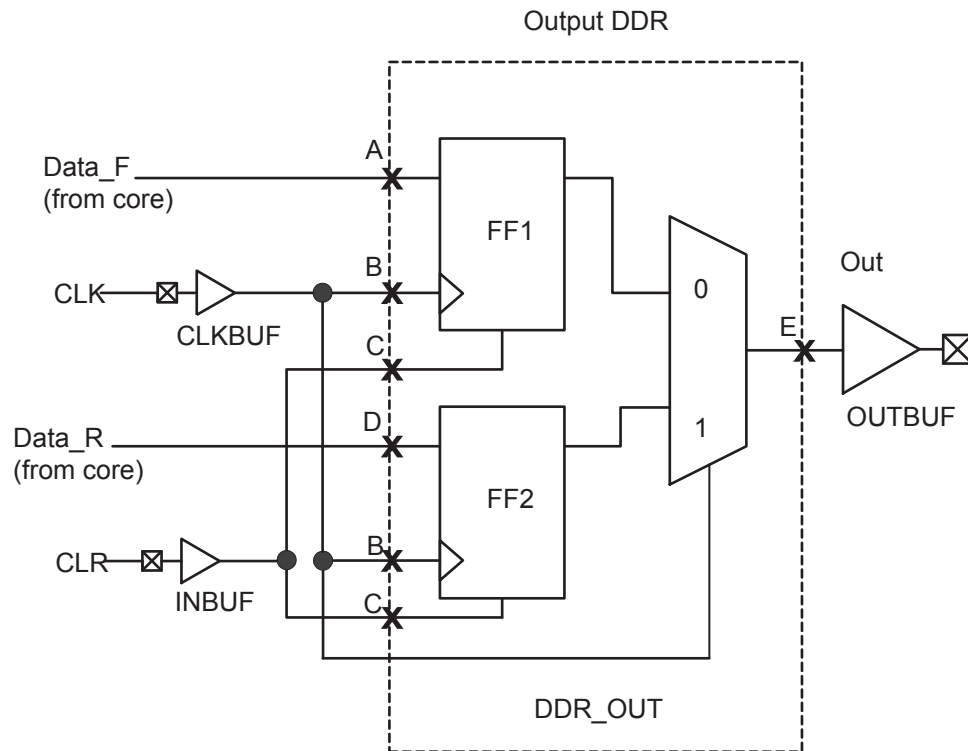


Figure 2-22 • Output DDR Timing Model

Table 2-103 • Parameter Definitions

Parameter Name	Parameter Definition	Measuring Nodes (from, to)
t_{DDROCLKQ}	Clock-to-Out	B, E
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out	C, E
$t_{\text{DDROREMCLR}}$	Clear Removal	C, B
$t_{\text{DDRORECCLR}}$	Clear Recovery	C, B
t_{DDROSUD1}	Data Setup Data_F	A, B
t_{DDROSUD2}	Data Setup Data_R	D, B
t_{DDROHD1}	Data Hold Data_F	A, B
t_{DDROHD2}	Data Hold Data_R	D, B

Table 2-109 • A3P060 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2		-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.71	0.93	0.81	1.05	0.95	1.24	ns
t_{RCKH}	Input High Delay for Global Clock	0.70	0.96	0.80	1.09	0.94	1.28	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-110 • A3P125 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2		-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.77	0.99	0.87	1.12	1.03	1.32	ns
t_{RCKH}	Input High Delay for Global Clock	0.76	1.02	0.87	1.16	1.02	1.37	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-111 • A3P250 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–2		–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.80	1.01	0.91	1.15	1.07	1.36	ns
t_{RCKH}	Input High Delay for Global Clock	0.78	1.04	0.89	1.18	1.04	1.39	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Table 2-112 • A3P400 Global Resource
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$

Parameter	Description	–2		–1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.87	1.09	0.99	1.24	1.17	1.46	ns
t_{RCKH}	Input High Delay for Global Clock	0.86	1.11	0.98	1.27	1.15	1.49	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.26		0.29		0.34	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

Timing Waveforms

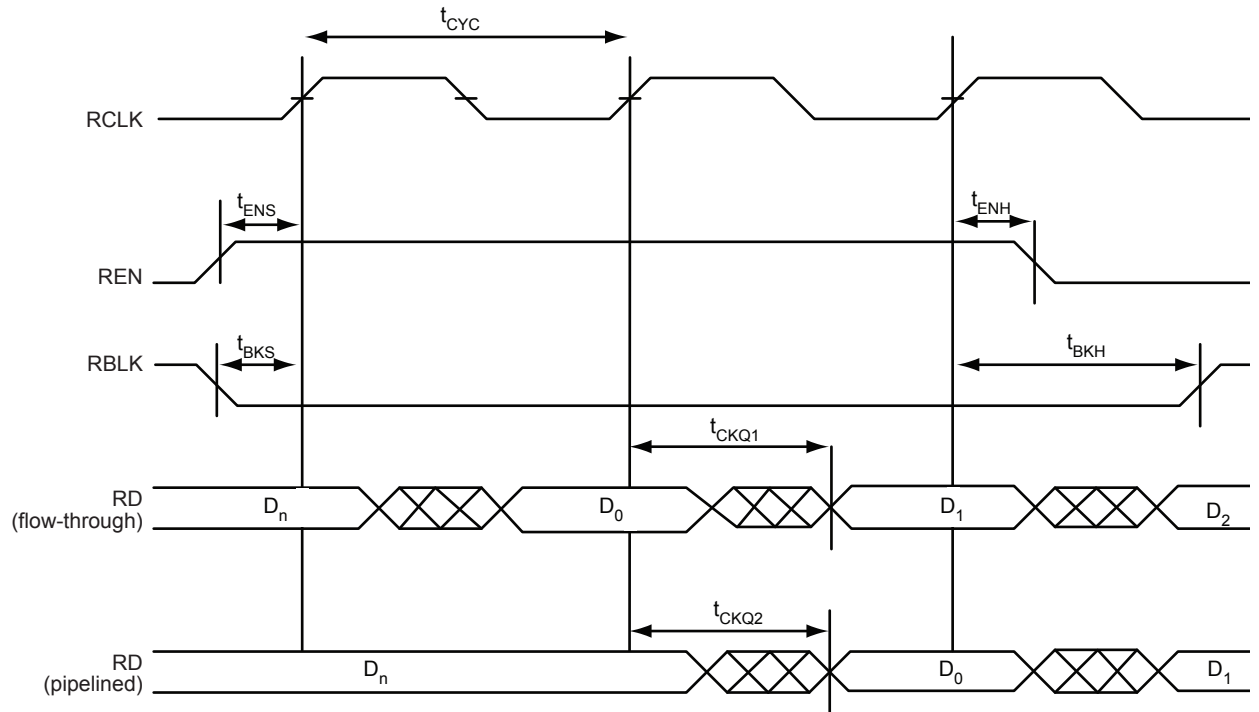


Figure 2-37 • FIFO Read

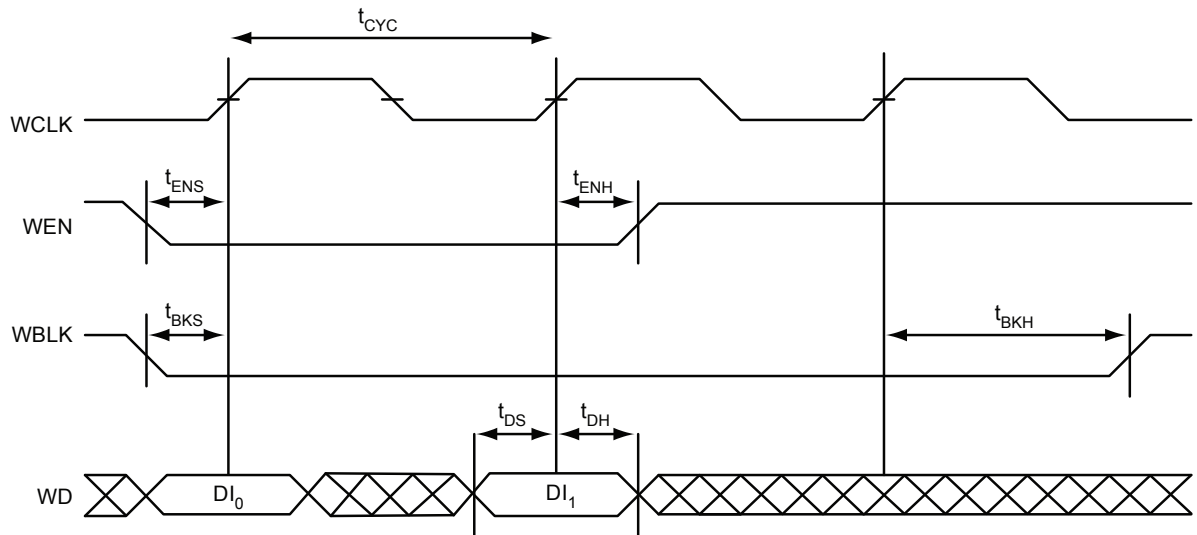
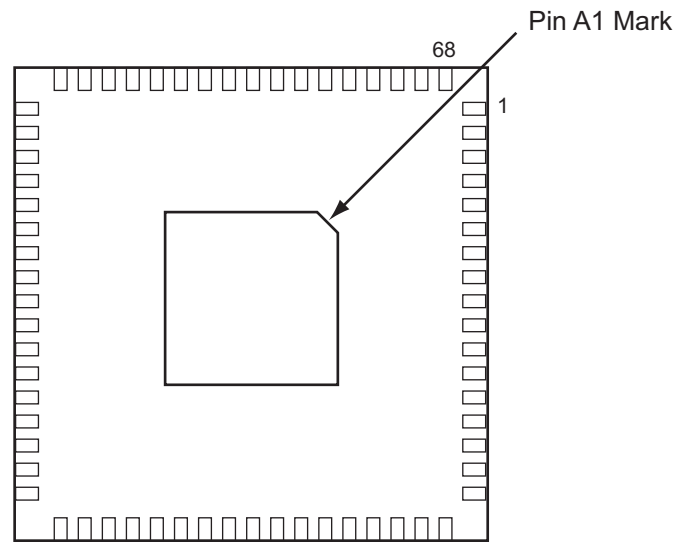


Figure 2-38 • FIFO Write

Table 2-121 • A3P250 FIFO 1k×4**Worst Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, $V_{CC} = 1.425\text{ V}$**

Parameter	Description	–2	–1	Std.	Units
t_{ENS}	REN, WEN Setup Time	4.05	4.61	5.42	ns
t_{ENH}	REN, WEN Hold Time	0.00	0.00	0.00	ns
t_{BKS}	BLK Setup Time	0.19	0.22	0.26	ns
t_{BKH}	BLK Hold Time	0.00	0.00	0.00	ns
t_{DS}	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
t_{DH}	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	2.36	2.68	3.15	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	0.89	1.02	1.20	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
t_{WCKFF}	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
t_{REMRSTB}	RESET Removal	0.29	0.33	0.38	ns
t_{RECRSTB}	RESET Recovery	1.50	1.71	2.01	ns
t_{MPWRSTB}	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
t_{CYC}	Clock Cycle Time	3.23	3.68	4.32	ns
F_{MAX}	Maximum Frequency for FIFO	310	272	231	MHz

QN68 – Bottom View



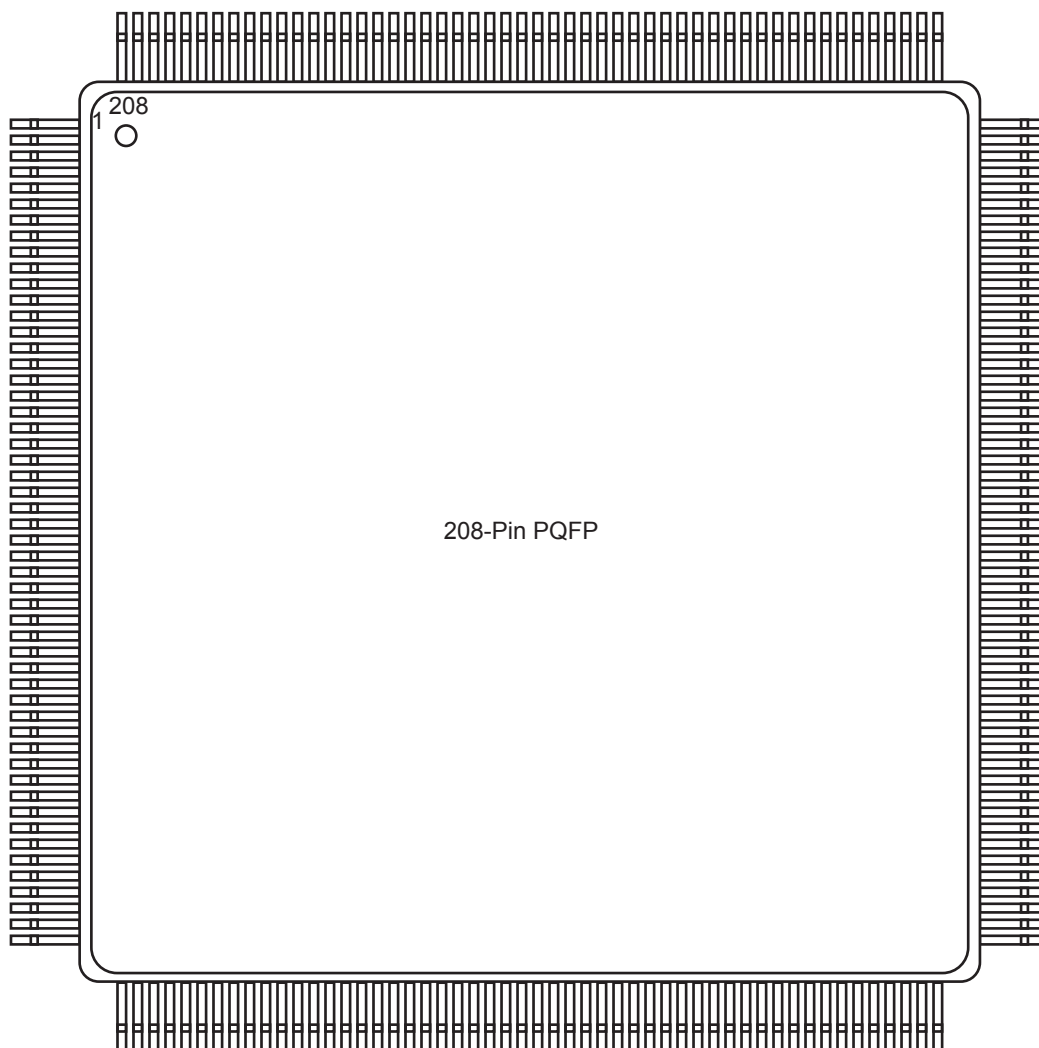
Note: The die attach paddle center of the package is tied to ground (GND).

Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

QN132	
Pin Number	A3P060 Function
C17	IO57RSB1
C18	NC
C19	TCK
C20	VMV1
C21	VPUMP
C22	VJTAG
C23	VCCIB0
C24	NC
C25	NC
C26	GCA1/IO42RSB0
C27	GCC0/IO39RSB0
C28	VCCIB0
C29	IO29RSB0
C30	GNDQ
C31	GBA1/IO27RSB0
C32	GBB0/IO24RSB0
C33	VCC
C34	IO19RSB0
C35	IO16RSB0
C36	IO13RSB0
C37	GAC1/IO10RSB0
C38	NC
C39	GAA0/IO05RSB0
C40	VMV0
D1	GND
D2	GND
D3	GND
D4	GND

PQ208 – Top View



Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

PQ208	
Pin Number	A3P250 Function
1	GND
2	GAA2/IO118UDB3
3	IO118VDB3
4	GAB2/IO117UDB3
5	IO117VDB3
6	GAC2/IO116UDB3
7	IO116VDB3
8	IO115UDB3
9	IO115VDB3
10	IO114UDB3
11	IO114VDB3
12	IO113PDB3
13	IO113NDB3
14	IO112PDB3
15	IO112NDB3
16	VCC
17	GND
18	VCCIB3
19	IO111PDB3
20	IO111NDB3
21	GFC1/IO110PDB3
22	GFC0/IO110NDB3
23	GFB1/IO109PDB3
24	GFB0/IO109NDB3
25	VCOMPLF
26	GFA0/IO108NPB3
27	VCCPLF
28	GFA1/IO108PPB3
29	GND
30	GFA2/IO107PDB3
31	IO107NDB3
32	GFB2/IO106PDB3
33	IO106NDB3
34	GFC2/IO105PDB3
35	IO105NDB3
36	NC

PQ208	
Pin Number	A3P250 Function
37	IO104PDB3
38	IO104NDB3
39	IO103PSB3
40	VCCIB3
41	GND
42	IO101PDB3
43	IO101NDB3
44	GEC1/IO100PDB3
45	GEC0/IO100NDB3
46	GEB1/IO99PDB3
47	GEB0/IO99NDB3
48	GEA1/IO98PDB3
49	GEA0/IO98NDB3
50	VMV3
51	GNDQ
52	GND
53	NC
54	NC
55	GEA2/IO97RSB2
56	GEB2/IO96RSB2
57	GEC2/IO95RSB2
58	IO94RSB2
59	IO93RSB2
60	IO92RSB2
61	IO91RSB2
62	VCCIB2
63	IO90RSB2
64	IO89RSB2
65	GND
66	IO88RSB2
67	IO87RSB2
68	IO86RSB2
69	IO85RSB2
70	IO84RSB2
71	VCC
72	VCCIB2

PQ208	
Pin Number	A3P250 Function
73	IO83RSB2
74	IO82RSB2
75	IO81RSB2
76	IO80RSB2
77	IO79RSB2
78	IO78RSB2
79	IO77RSB2
80	IO76RSB2
81	GND
82	IO75RSB2
83	IO74RSB2
84	IO73RSB2
85	IO72RSB2
86	IO71RSB2
87	IO70RSB2
88	VCC
89	VCCIB2
90	IO69RSB2
91	IO68RSB2
92	IO67RSB2
93	IO66RSB2
94	IO65RSB2
95	IO64RSB2
96	GDC2/IO63RSB2
97	GND
98	GDB2/IO62RSB2
99	GDA2/IO61RSB2
100	GNDQ
101	TCK
102	TDI
103	TMS
104	VMV2
105	GND
106	VPUMP
107	NC
108	TDO

FG144	
Pin Number	A3P250 Function
K1	GEB0/IO99NDB3
K2	GEA1/IO98PDB3
K3	GEA0/IO98NDB3
K4	GEA2/IO97RSB2
K5	IO90RSB2
K6	IO84RSB2
K7	GND
K8	IO66RSB2
K9	GDC2/IO63RSB2
K10	GND
K11	GDA0/IO60VDB1
K12	GDB0/IO59VDB1
L1	GND
L2	VMV3
L3	GEB2/IO96RSB2
L4	IO91RSB2
L5	VCCIB2
L6	IO82RSB2
L7	IO80RSB2
L8	IO72RSB2
L9	TMS
L10	VJTAG
L11	VMV2
L12	TRST
M1	GNDQ
M2	GEC2/IO95RSB2
M3	IO92RSB2
M4	IO89RSB2
M5	IO87RSB2
M6	IO85RSB2
M7	IO78RSB2
M8	IO76RSB2
M9	TDI
M10	VCCIB2
M11	VPUMP
M12	GNDQ

Revision	Changes	Page
Revision 10 (continued)	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-28 • I/O Output Buffer Maximum Resistances ¹ through Table 2-30 • I/O Output Buffer Maximum Resistances ¹ was replaced by "Same as regular 3.3 V" (SAR 33852).	2-26 to 2-28
	The equations in the notes for Table 2-31 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 32470).	2-28
	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-32 • I/O Short Currents IOSH/IOSL through Table 2-34 • I/O Short Currents IOSH/IOSL was replaced by "Same as regular 3.3 V LVCMOS" (SAR 33852).	2-29 to 2-31
	In the " 3.3 V LVCMOS Wide Range " section, values were added to Table 2-47 through Table 2-49 for IOSL and IOSH, replacing "TBD" (SAR 33852).	2-39 to 2-40
	The following sentence was deleted from the " 2.5 V LVCMOS " section (SAR 24916): "It uses a 5 V–tolerant input buffer and push-pull output buffer."	2-47
	The table notes were revised for Table 2-90 • LVDS Minimum and Maximum DC Input and Output Levels (SAR 33859).	2-66
	Values were added for $F_{DDRIMAX}$ and F_{DDOMAX} in Table 2-102 • Input DDR Propagation Delays and Table 2-104 • Output DDR Propagation Delays (SAR 23919).	2-78, 2-80
	Table 2-115 • ProASIC3 CCC/PLL Specification was updated. A note was added to indicate that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 25705).	2-90
	The following figures were deleted (SAR 29991). Reference was made to a new application note, <i>Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs</i> , which covers these cases in detail (SAR 21770). Figure 2-34 • Write Access after Write onto Same Address Figure 2-35 • Read Access after Write onto Same Address Figure 2-35 • Read Access after Write onto Same Address The port names in the SRAM " Timing Waveforms ", SRAM " Timing Characteristics " tables, Figure 2-39 • FIFO Reset , and the FIFO " Timing Characteristics " tables were revised to ensure consistency with the software names (SARs 29991, 30510).	2-92, 2-94, 2-99 2-102
July 2010	The " Pin Descriptions " chapter has been added (SAR 21642).	3-1
	Package names used in the " Package Pin Assignments " section were revised to match standards given in Package Mechanical Drawings (SAR 27395).	4-1
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The " ProASIC3 Device Status " table on page IV indicates the status for each device in the device family.	N/A

Revision	Changes	Page	
Revision 9 (Oct 2009) Product Brief v1.3	The CS121 package was added to table under "Features and Benefits" section, the "I/Os Per Package 1" table, Table 1 • ProASIC3 FPGAs Package Sizes Dimensions, "ProASIC3 Ordering Information", and the "Temperature Grade Offerings" table.	I – IV	
	"ProASIC3 Ordering Information" was revised to include the fact that some RoHS compliant packages are halogen-free.	IV	
	Packaging v1.5	The "CS121 – Bottom View" figure and pin table for A3P060 are new.	4-15
Revision 8 (Aug 2009) Product Brief v1.2	All references to M7 devices (CoreMP7) and speed grade –F were removed from this document.	N/A	
	Table 1-1 I/O Standards supported is new.	1-7	
	The I/Os with Advanced I/O Standards section was revised to add definitions of hot-swap and cold-sparing.	1-7	
	DC and Switching Characteristics v1.4	3.3 V LVCMOS and 1.2 V LVCMOS Wide Range support was added to the datasheet. This affects all tables that contained 3.3 V LVCMOS and 1.2 V LVCMOS data.	N/A
	I _{IL} and I _{IH} input leakage current information was added to all "Minimum and Maximum DC Input and Output Levels" tables.	N/A	
	–F was removed from the datasheet. The speed grade is no longer supported.	N/A	
	The notes in Table 2-2 • Recommended Operating Conditions 1 were updated.	2-2	
	Table 2-4 • Overshoot and Undershoot Limits 1 was updated.	2-3	
	Table 2-6 • Temperature and Voltage Derating Factors for Timing Delays was updated.	2-6	
	In Table 2-116 • RAM4K9, the following specifications were removed: t _{WRO} t _{CCKH}	2-96	
In Table 2-117 • RAM512X18, the following specifications were removed: t _{WRO} t _{CCKH}	2-97		
In the title of Table 2-74 • 1.8 V LVCMOS High Slew, VCCI had a typo. It was changed from 3.0 V to 1.7 V.	2-58		
Revision 7 (Feb 2009) Product Brief v1.1	The "Advanced I/O" section was revised to add a bullet regarding wide range power supply voltage support.	I	
	The table under "Features and Benefits" section, was updated to include a value for typical equivalent macrocells for A3P250.	I	
	The QN48 package was added to the following tables: the table under "Features and Benefits" section, "I/Os Per Package 1" "ProASIC3 FPGAs Package Sizes Dimensions", and "Temperature Grade Offerings". The number of singled-ended I/Os for QN68 was added to the "I/Os Per Package 1" table.	N/A	
	The Wide Range I/O Support section is new.	1-7	
Revision 6 (Dec 2008) Packaging v1.4	The "QN48 – Bottom View" section is new.	4-1	
	The "QN68" pin table for A3P030 is new.	4-5	

Revision	Changes	Page
Advance v0.6 (continued)	The "RESET" section was updated.	2-25
	The "WCLK and RCLK" section was updated.	2-25
	The "RESET" section was updated.	2-25
	The "RESET" section was updated.	2-27
	The "Introduction" of the "Advanced I/Os" section was updated.	2-28
	The "I/O Banks" section is new. This section explains the following types of I/Os: Advanced Standard+ Standard Table 2-12 • Automotive ProASIC3 Bank Types Definition and Differences is new. This table describes the standards listed above.	2-29
	PCI-X 3.3 V was added to the Compatible Standards for 3.3 V in Table 2-11 • VCCI Voltages and Compatible Standards	2-29
	Table 2-13 • ProASIC3 I/O Features was updated.	2-30
	The "Double Data Rate (DDR) Support" section was updated to include information concerning implementation of the feature.	2-32
	The "Electrostatic Discharge (ESD) Protection" section was updated to include testing information.	2-35
	Level 3 and 4 descriptions were updated in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices.	2-64
	The notes in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices were updated.	2-64
	The "Simultaneous Switching Outputs (SSOs) and Printed Circuit Board Layout" section is new.	2-41
	A footnote was added to Table 2-14 • Maximum I/O Frequency for Single-Ended and Differential I/Os in All Banks in Automotive ProASIC3 Devices (maximum drive strength and high slew selected).	2-30
	Table 2-18 • Automotive ProASIC3 I/O Attributes vs. I/O Standard Applications	2-45
	Table 2-50 • ProASIC3 Output Drive (OUT_DRIVE) for Standard I/O Bank Type (A3P030 device)	2-83
	Table 2-51 • ProASIC3 Output Drive for Standard+ I/O Bank Type was updated.	2-84
	Table 2-54 • ProASIC3 Output Drive for Advanced I/O Bank Type was updated.	2-84
	The "x" was updated in the "User I/O Naming Convention" section.	2-48
	The "VCC Core Supply Voltage" pin description was updated.	2-50
	The "VMVx I/O Supply Voltage (quiet)" pin description was updated to include information concerning leaving the pin unconnected.	2-50
	The "VJTAG JTAG Supply Voltage" pin description was updated.	2-50
	The "VPUMP Programming Supply Voltage" pin description was updated to include information on what happens when the pin is tied to ground.	2-50
	The "I/O User Input/Output" pin description was updated to include information on what happens when the pin is unused.	2-50
	The "JTAG Pins" section was updated to include information on what happens when the pin is unused.	2-51

Revision	Changes	Page
Advance v0.3	The "PLL Macro" section was updated. EXTFB information was removed from this section.	2-15
	The CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT} was updated in Table 2-11 • ProASIC3 CCC/PLL Specification	2-29
	EXTFB was removed from Figure 2-27 • CCC/PLL Macro.	2-28
	Table 2-13 • ProASIC3 I/O Features was updated.	2-30
	The "Hot-Swap Support" section was updated.	2-33
	The "Cold-Sparing Support" section was updated.	2-34
	"Electrostatic Discharge (ESD) Protection" section was updated.	2-35
	The LVPECL specification in Table 2-43 • I/O Hot-Swap and 5 V Input Tolerance Capabilities in ProASIC3 Devices was updated.	2-64
	In the Bank 1 area of Figure 2-72, VMV2 was changed to VMV1 and VCCIB2 was changed to VCC _I B1.	2-97
	The VJTAG and I/O pin descriptions were updated in the "Pin Descriptions" section.	2-50
	The "JTAG Pins" section was updated.	2-51
	"128-Bit AES Decryption" section was updated to include M7 device information.	2-53
	Table 3-6 was updated.	3-6
	Table 3-7 was updated.	3-6
	In Table 3-11, PAC4 was updated.	3-93-8
	Table 3-20 was updated.	3-20
	The note in Table 3-32 was updated.	3-27
	All Timing Characteristics tables were updated from LVTTTL to Register Delays	3-31 to 3-73
	The Timing Characteristics for RAM4K9, RAM512X18, and FIFO were updated.	3-85 to 3-90
	F_{TCKMAX} was updated in Table 3-110.	3-97
Advance v0.2	Figure 2-11 was updated.	2-9
	The "Clock Resources (VersaNets)" section was updated.	2-9
	The "VersaNet Global Networks and Spine Access" section was updated.	2-9
	The "PLL Macro" section was updated.	2-15
	Figure 2-27 was updated.	2-28
	Figure 2-20 was updated.	2-19
	Table 2-5 was updated.	2-25
	Table 2-6 was updated.	2-25
	The "FIFO Flag Usage Considerations" section was updated.	2-27
	Table 2-13 was updated.	2-30
	Figure 2-24 was updated.	2-31
	The "Cold-Sparing Support" section is new.	2-34